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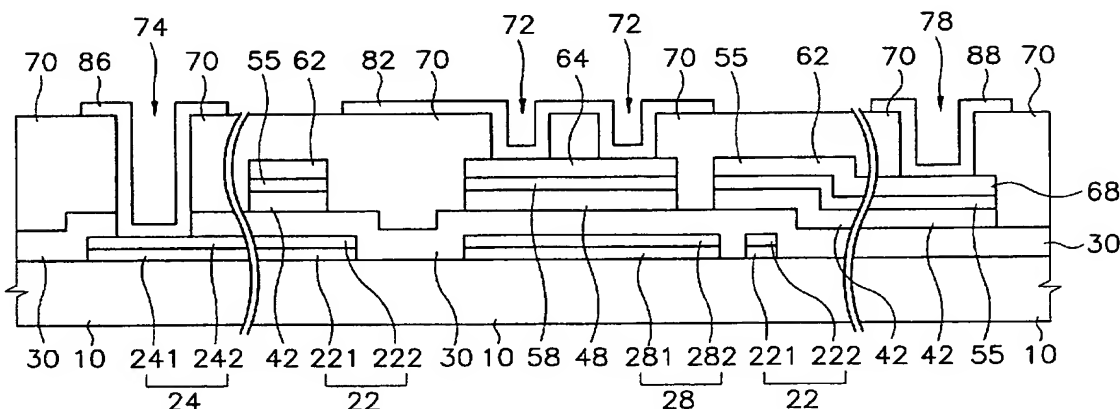
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(54) Title: STRIPPING COMPOSITION FOR REMOVING A PHOTORESIST AND METHOD OF MANUFACTURING TFT
SUBSTRATE FOR A LIQUID CRYSTAL DISPLAY DEVICE USING THE SAME



(57) Abstract: In a stripping composition for easily removing a photoresist without an adverse effect and a method of manufacturing a TFT substrate for an LCD device using the same, the stripping composition includes acetic acid and ozone gas contained in the acetic acid as a bubble form to remove the photoresist including novolak. A photoresist pattern including novolak is formed on a predetermined layer (24) formed on a substrate (10). The layer is etched using the photoresist pattern as a mask to form a pattern of the layer. The photoresist pattern is removed using the stripping composition. The stripping composition is cheap and more effectively protects the environment in comparison with the conventional stripping compositions. Additionally, an O₂ ashing process performed before or after a stripping process may be omitted to thereby simplify a stripping process.

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